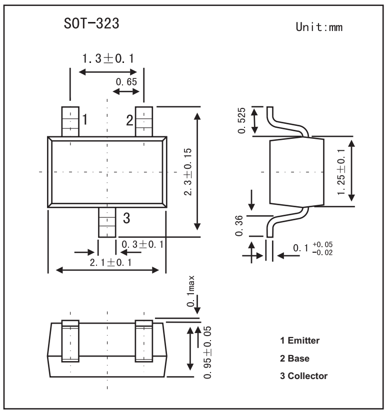
PNP silicon Transistor

2SA1576

■ Features

- ● Low noise:NF=0.5dB(TYP.)
- ● Epitaxial planar type.



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-40	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-100	A
Collector power dissipation	P_C	200	W
Junction temperature	T_j	125	℃
Storage temperature	T_{stg}	-55 to +125	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV_{CBO}	I_C=-50μA	-50			V
Collector-emitter breakdown voltage	BV_{CEO}	I_C=-1mA	-40			V
Emitter-base breakdown voltage	BV_{EBO}	I_E=-50μA	-5			V
Collector cutoff current	I_{CBO}	V_{CB}=-30V			-0.5	μA
Emitter cutoff current	I_{EBO}	V_{EB}=-4V			-0.5	μA
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C/I_B=-50mA/-5mA			-0.5	V
DC current transfer ratio	h_{FE}	V_{CE}=-6V, I_C=-1mA	120		560	
Transition frequency	f_T	V_{CE}=-12V, I_E=2mA		140		MHz
Output capacitance	C_{ob}	V_{CB}=-12V, I_E=0A, f=1MHz		3.5		pF

■ h_{FE} Classification

Marking	Q	R	S
h_{FE}	120～270	180～390	270～560